L Number	Hits	Search Text	DB	Time stamp
1	57		USPAT;	2004/06/12 14:23
		nonvolatile) near2 memory	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	IBM_TDB	2004/06/12 14:25
2	45		USPAT;	2004/06/12 14:25
		nonvolatile) near2 memory and method.clm.	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
3	6	chalcogenide adj glass.ti,ab,clm. and	USPĀT;	2004/06/12 14:27
		(non-volatile nonvolatile) near2	US-PGPUB;	
		memory.ti,ab,clm. and method.clm.	EPO; JPO;	
!			DERWENT;	
			IBM_TDB	0004/06/10 14 00
4	3715		USPAT;	2004/06/12 14:29
		(257/299) or (257/300) or (257/63) or	US-PGPUB	
		(257/52) or (257/55) or (257/2) or (501/11) or (501/19) or (501/42)).CCLS.		
5	8	(((257/296) or (257/297) or (257/298) or	USPAT;	2004/06/12 14:29
		((257/299) or (257/300) or (257/63) or	US-PGPUB;	
		(257/52) or (257/55) or (257/2) or	EPO; JPO;	
		(501/11) or (501/19) or (501/42)).CCLS.)	DERWENT;	
		and germanium and selenide and (silver ag)	IBM_TDB	
}		and (non-volatile nonvolatile) near2		
		memory	HODAM.	2004/06/11 14.50
_	0	, , , , , , , , , , , , , , , , , , , ,	USPAT; US-PGPUB;	2004/06/11 14:58
		chalcogenide.ti.").PN.	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	24	chalcogenide adj glass.clm. and	USPAT;	2002/09/17 10:05
		chalcogenide.ti.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	3	+:	IBM_TDB USPAT;	2002/09/17 10:06
-	3	pcram.ti.	US-PGPUB;	2002/03/17 10:00
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	pcram.ti,ab,clm. and processor.clm.	USPAT;	2002/09/17 10:07
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	1285	ram near3 processor.ti,ab.	IBM_TDB USPAT;	2002/09/17 10:07
	1203	lam nears processor.er, ab.	US-PGPUB;	2002,00,17 10.07
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	209	ram near3 processor.ti.	USPAT;	2002/09/17 10:07
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	5	ram near3 processor.ti. and processor.clm.	USPAT;	2002/09/17 10:24
			US-PGPUB;	
]		·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	36	chalcogenide near4 use	USPAT;	2002/09/17 10:26
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
		L		L

_	0	chalcolgenide near6 (dop\$3 or impurit\$3)	USPAT;	2002/12/19 14:29
		near6 (metal or silver or ag or copper or	US-PGPUB;	
		cu or platinum or pt or gold or au or	EPO; JPO;	
		cadmium or cd or ruthenium or ru or coablt	DERWENT;	
		or co or zinc or zn or chromium or cr or	IBM_TDB	
		manganese or mn or nickel or ni) and		
		memory adj2 (cell or device).ti,ab,clm.		0000/10/16 15 51
_	0	chalcolgenide adj glass near12 (metal or	USPAT;	2002/12/16 15:51
		silver or ag or copper or cu or platinum	US-PGPUB;	
		or pt or gold or au or cadmium or cd or	EPO; JPO;	
		ruthenium or ru or cobalt or co or zinc or	DERWENT;	
	}	zn or chromium or cr or manganese or mn or	IBM_TDB	
		nickel or ni) and memory adj2 (cell or		
	0	device).ti,ab,clm.	USPAT;	2002/12/16 15:51
-		chalcolgenide adj glass and (metal or silver or ag or copper or cu or platinum	US-PGPUB;	2002/12/10 13.31
		or pt or gold or au or cadmium or cd or	EPO; JPO;	
		ruthenium or ru or cobalt or co or zinc or	DERWENT;	
İ		zn or chromium or cr or manganese or mn or	IBM TDB	
1		nickel or ni) and memory adj2 (cell or	1511-155	
		device).ti,ab,clm.		
I _	2	chalcogenide adj glass near12 (metal or	USPAT;	2002/12/16 16:33
		silver or ag or copper or cu or platinum	US-PGPUB;	
		or pt or gold or au or cadmium or cd or	EPO; JPO;	
		ruthenium or ru or cobalt or co or zinc or	DERWENT;	
		zn or chromium or cr or manganese or mn or	IBM TDB	
		nickel or ni) and memory adj2 (cell or		
		device).ti,ab,clm.		
-	21	chalcogenide adj glass near12 (metal or	USPAT;	2002/12/16 16:36
		silver or ag or copper or cu or platinum	US-PGPUB;	
		or pt or gold or au or cadmium or cd or	EPO; JPO;	
		ruthenium or ru or cobalt or co or zinc or	DERWENT;	
		zn or chromium or cr or manganese or mn or	IBM_TDB	
		nickel or ni) and 257/\$6.ccls.	-	
-	115	(365/153).CCLS.	USPAT;	2002/12/17 15:34
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
]	_	(4255 (252) 2525 ) ) ) )	IBM_TDB	0000/10/15 15 51
-	6	((365/153).CCLS.) and chalcogenide	USPAT;	2002/12/17 15:51
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
<u> </u>	2	ag add content and chalcogonide and memory	IBM_TDB USPAT;	2002/12/17 16:03
_	2	ag adj content and chalcogenide and memory	US-PGPUB;	2002/12/1/ 10:03
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	ag adj content and "ag-ge-te" and memory	USPAT;	2002/12/17 16:06
		ag aa, concern and ag go to and memory	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	45	chalcogenide adj glass and (silver or ag)	USPĀT;	2002/12/17 16:07
		and memory	US-PGPUB;	
		•	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	3	1 3 3 3 1	USPĀT;	2002/12/17 16:39
		near4 (content or concentration) and	US-PGPUB;	
		memory	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	7	(US-3810128-\$ or US-5479382-\$ or	USPAT;	2002/12/17 16:41
		US-6084796-\$ or US-6487106-\$ or	US-PGPUB	
		US-3827033-\$ or US-3721838-\$).did. or		
		(US-20020168820-\$).did.		0000/10/15 15 15
-	0	, ,	USPAT;	2002/12/17 16:43
]		(percentage or concentration or content)	US-PGPUB	2002/12/17 16 11
-	0	"ge se.sub.3" and (silver or ag) near6	USPAT;	2002/12/17 16:44
I		(percentage or concentration or content)	US-PGPUB	

			,	
-	0	"ge se.sub."\$1 and (silver or ag) near6	EPO; JPO;	2002/12/17 16:50
		(percentage or concentration or content)	DERWENT; IBM TDB	
1_	1	("6487106").PN.	USPAT;	2002/12/18 16:09
	1	( 0407100 )	US-PGPUB;	2002,12,10 10:03
			EPO; JPO;	
			DERWENT;	
	İ		IBM_TDB	
-	2		USPAT;	2002/12/18 17:48
		ag) and chalcogenide adj glass and memory	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	119	(tie adj line or tie-line) and phase adj	USPAT;	2002/12/19 10:35
	123	diagram	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	9	'	USPAT;	2002/12/19 11:07
1		phase adj diagram	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	0	("kozicki.in.").PN.	USPAT;	2002/12/19 11:07
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/10/10 11 10
-	39	kozicki.in.	USPAT;	2002/12/19 11:12
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	5	(("5761115") or ("5896312") or ("5914893")	USPĀT;	2002/12/19 11:15
		or ("6084796")).PN.	US-PGPUB;	
			EPO; JPO;	
İ			DERWENT;	
	1	("6469364").PN.	IBM_TDB USPAT;	2002/12/19 11:15
-	1	( 0409304 ).FN.	US-PGPUB;	2002/12/19 11:15
			EPO; JPO;	,
			DERWENT;	
			IBM_TDB	
-	18	(US-6084796-\$ or US-6487106-\$ or	USPAT;	2002/12/19 11:16
		US-3721838-\$ or US-3810128-\$ or	US-PGPUB;	
		US-3827033-\$ or US-6418049-\$ or US-5479382-\$ or US-6469364-\$ or	DERWENT	
		US-6388324-\$ or US-5914893-\$ or		
	]	US-5896312-\$ or US-5761115-\$ or		
		US-5500532-\$ or US-5314772-\$).did. or		
		(US-20020000666-\$ or US-20020190350-\$ or		
		US-20020168820-\$).did. or		
	2	(US-5761115-\$).did. ("6348365").PN.	HCDATT -	2002/12/19 12:02
-	2	( 0040000 ).FN.	USPAT; US-PGPUB;	2002/12/19 12:02
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	("6418049").PN.	USPĀT;	2002/12/19 12:02
			US-PGPUB;	
			EPO; JPO;	
1	]		DERWENT; IBM TDB	
_	0	switching adj field and chalcogenide adj	USPAT;	2002/12/19 14:31
1		glass and memory and ("Ag-Ge-Se" or	US-PGPUB;	
1		(silver or ag) near3 (percent or	EPO; JPO;	
1		percentage))	DERWENT;	
			IBM_TDB	

_	7	switching adj field and chalcogenide adj	USPAT;	2002/12/19 15:38
		glass and memory	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	4	switching adj speed and chalcogenide adj	USPAT;	2002/12/19 15:41
		glass and memory and (silver or ag)	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	36	switching and chalcogenide adj glass and	USPĀT;	2002/12/19 16:59
		memory and (silver or ag)	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	16042	non-volatile adj memory.ti,ab.,clm. and	USPAT;	2002/12/19 17:02
	10012	(germanium adj selenide or "ge.sub.x	US-PGPUB;	
		se.sub.1-x" or "Ag-Ge-Se" or (silver or	EPO; JPO;	
		ag) near6 chalcogenide)	DERWENT;	
	16042	non volatile adi memoru ti ab alm and	IBM_TDB   USPAT;	2002/12/19 17:06
-	16042	non-volatile adj memory.ti,ab.,clm. and (germanium adj selenide or "ge.sub.x	US-PGPUB;	2002/12/19 17:00
		se.sub.1-x" or "Ag-Ge-Se" or ((silver or	EPO; JPO;	
1	]	ag) near6 chalcogenide))	DERWENT;	
			IBM_TDB	0000/10/10 15 15
-	16042		USPAT;	2002/12/19 17:07
		(germanium adj selenide or "ge.sub.x se.sub.1-x" or "Ag-Ge-Se" or (silver or	US-PGPUB; EPO; JPO;	
		ag) near6 chalcogenide)	DERWENT;	
		,	IBM TDB	
-	1		USPAT;	2002/12/19 18:22
		(germanium adj selenide or "ge.sub.x	US-PGPUB;	
		se.sub.1-x" or "Ag-Ge-Se" or (silver or ag) near6 chalcogenide)	EPO; JPO; DERWENT;	
		agy heart charcogeniae,	IBM TDB	
_	231	(dendrite or dendritic) near12 voltage or	USPĀT;	2002/12/19 18:24
		electric adj field near12 chalcogenide adj	US-PGPUB;	
		glass	EPO; JPO;	
			DERWENT; IBM TDB	
_	157	(dendrite or dendritic) near6 voltage or	USPAT;	2002/12/19 18:24
		electric adj field near6 chalcogenide adj	US-PGPUB;	
		glass	EPO; JPO;	
			DERWENT;	
_	0	(dendrite or dendritic) near6 (voltage or	IBM_TDB USPAT;	2002/12/19 18:25
	ĺ	electric adj field) near6 chalcogenide adj	US-PGPUB;	
		glass	EPO; JPO;	
1			DERWENT;	
_	0	   (dendrite or dendritic) near12 (voltage or	IBM_TDB USPAT;	2002/12/19 18:25
-		electric adj field) near12 chalcogenide	US-PGPUB;	2002/12/13 10.23
		adj glass	EPO; JPO;	
1			DERWENT;	]
	_	(dandaika an dandaiki a) 40 / 3/	IBM_TDB	2002/12/12 12 22
-	3	(dendrite or dendritic) near12 (voltage or electric adj field) and chalcogenide adj	USPAT; US-PGPUB;	2002/12/19 18:33
1		glass.ti,ab.	EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	0	("t.sub.g" of transition adj temperature)	USPAT;	2002/12/19 18:35
		near12 chalcogenide adj glass and photodiffusion	US-PGPUB; EPO; JPO;	
		p	DERWENT;	
			IBM_TDB	
-	0	("t.sub.g" or transition adj temperature)	USPAT;	2002/12/19 18:36
		near12 chalcogenide adj glass and	US-PGPUB;	
		photodiffusion	EPO; JPO; DERWENT;	
			IBM TDB	
	L			<u></u>

_	0	("t.sub.g" or temperature) near12	USPAT;	2002/12/19 18:36
	1	chalcogenide adj glass and photodiffusion	US-PGPUB;	
į			EPO; JPO;	
	İ		DERWENT; IBM TDB	
_	50	("t.sub.g" or temperature) near12	USPAT;	2002/12/19 18:41
_	30	chalcogenide adj glass	US-PGPUB;	2002/12/13 10:41
1	1	Charcogeniue adj grass	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	photodissolution near12 chalcogenide	USPAT;	2002/12/19 18:42
		near12 silver	US-PGPUB;	
}			EPO; JPO;	į
			DERWENT;	
			IBM_TDB	
-	3	photodissolution near12 silver	USPAT;	2002/12/19 18:42
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/12/20 15:30
_	0	microelectronic adj programmable adj	USPAT;	2002/12/20 15:39
		device and processor	US-PGPUB; EPO; JPO;	
	1		DERWENT;	
	1		IBM TDB	
_	3	pcram and processor .	USPAT;	2002/12/20 16:27
		posan and processor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	799	campbell.in. and memory	USPĀT;	2002/12/20 16:27
		-	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
j -	7	PCRAM.ti,ab.	USPAT;	2002/12/20 16:42
		,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	4867	   (programmable adj2 device or PCRAM).ti,ab.	IBM_TDB USPAT;	2002/12/20 16:43
-	4007	(programmable adjz device of rckar).ci,ab.	US-PGPUB;	2002/12/20 10.43
			EPO; JPO;	
			DERWENT;	
	i		IBM TDB	
_	214	(programmable adj memory adj device or	USPAT;	2002/12/20 16:44
		PCRAM).ti,ab.	US-PGPUB;	
		· '	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	'L9	USPAT;	2002/12/20 18:18
		PCRAM).ti,ab. and chalcogenide adj glass	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		], . , . , , , , , , , , , , ,	IBM_TDB	0000/10/00 10 15
<del>-</del>	0	kristy.in. and campbell.in. and	USPAT;	2002/12/20 18:19
		chalcogenide	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
	0	kristy.in. and campbell.in.	USPAT;	2002/12/20 18:19
	]	Allocy.in. and campocit.in.	US-PGPUB;	2002,12,20 10.19
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1	campbell.in. and chalcogenide	USPAT;	2002/12/20 18:20
		· ·	US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
.			IBM TDB	

-	1	("ge.sub.x se.sub.1-x" or "ge.sub.y.	USPAT;	2002/12/20 18:28
		se.sub.1-y" or "ag-ge-se") and glass and	US-PGPUB;	
		(silver or ag) and memory	EPO; JPO;	
	ĺ		DERWENT;	
		(Here sub as as sub 1 all on the sub as	IBM_TDB	2002/12/20 18:52
-	2	("ge.sub.x se.sub.1-x" or "ge.sub.y.	USPAT;	2002/12/20 18:52
	1	se.sub.1-y" or "ag-ge-se" or "ge.sub.3	US-PGPUB;	
		se.sub.7") and glass and (silver or ag)	EPO; JPO;	
		and memory	DERWENT; IBM TDB	
		/lles sub w so sub 1 wll on lles sub w	USPAT;	2002/12/20 18:57
_	4	("ge.sub.x se.sub.1-x" or "ge.sub.y. se.sub.1-y" or "ag-ge-se" or	US-PGPUB;	2002/12/20 18.5/
		"ge.sub."?"se.sub."?) and glass and	EPO; JPO;	
		(silver or ag) and memory	DERWENT;	
Į		(Silver or ag, and memory	IBM TDB	
_	,	("5761115").PN.	USPAT;	2002/12/20 20:47
		( 3/01113 ).111.	US-PGPUB;	2002/12/20 20.4/
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
l <u>-</u>	27	chalcogenide adj glass near5	USPAT;	2002/12/20 20:48
	1	oxide.ti,ab,clm.	US-PGPUB;	2002/12/20 20:10
	}		EPO; JPO;	
	]		DERWENT;	
Į.			IBM TDB	
-	0	chalcogenide adj glass near5	USPAT;	2002/12/20 20:49
		oxide.ti,ab,clm. and memory.ti,ab,clm.	US-PGPUB;	,,
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	chalcogenide adj glass near5	USPAT;	2002/12/20 20:49
		oxide.ti,ab,clm. and storage.ti,ab,clm.	US-PGPUB;	l i
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	692	((257/2) or (257/52) or (257/55) or	USPAT;	2002/12/21 11:59
		(257/63) or (257/298)).CCLS.	US-PGPUB	
-	11	1 ( , , = , , , , , , , , , , , , , , , ,	USPAT;	2002/12/21 12:00
		(257/63) or (257/298)).CCLS.) and	US-PGPUB;	
		chalcogenide adj glass and memory	EPO; JPO;	
			DERWENT;	İ
	_	44405740	IBM_TDB	
-	5		USPAT;	2002/12/21 12:01
		(257/63) or (257/298)).CCLS.) and	US-PGPUB;	
		chalcogenide adj glass and	EPO; JPO;	
		memory.ti,ab,clm.	DERWENT;	
_	95	(365/163).CCLS.	IBM_TDB USPAT;	2002/12/21 12:01
	)	(303) 103) . 0010 .	US-PGPUB;	2002/12/21 12:01
[			EPO; JPO;	
1			DERWENT;	
			IBM TDB	
_	57	((365/163).CCLS.) and chalcogenide	USPĀT;	2002/12/21 12:01
			US-PGPUB;	
.			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	59	((((257/2) or (257/52) or (257/55) or	USPĀT;	2002/12/21 12:03
]		(257/63) or (257/298)).CCLS.) and	US-PGPUB;	
		chalcogenide adj glass and	EPO; JPO;	
		memory.ti,ab,clm.) or (((365/163).CCLS.)	DERWENT;	
		and chalcogenide)	IBM_TDB	
<b>-</b>	5		USPAT;	2002/12/21 12:04
		(257/63) or (257/298)).CCLS.) and	US-PGPUB;	
		chalcogenide adj glass and	EPO; JPO;	
	i	memory.ti,ab,clm.) or (((365/163).CCLS.)	DERWENT;	
		and chalcogenide)) and silver	IBM_TDB	<u> </u>

<del></del>		T (*** 550 550 A *** 5241 200 A ***	L HODAM.	1 2002 /12 /21 12 - 50 1
_	31	(US-5596522-\$ or US-5341328-\$ or US-5166758-\$ or US-6487113-\$ or	USPAT; US-PGPUB;	2002/12/21 12:59
,		US-6462984-\$ or US-5072423-\$ or	JPO;	
		US-5272667-\$ or US-5363329-\$ or	DERWENT	
		US-5406509-\$ or US-5314772-\$ or		
		US-6487106-\$ or US-6469364-\$ or		
		US-3721838-\$ or US-3810128-\$ or		
		US-3827033-\$ or US-6348365-\$ or US-6084796-\$ or US-5914893-\$ or		
		US-5896312-\$ or US-5479382-\$ or		
		US-6418049-\$ or US-5761115-\$ or		
		US-6388324-\$ or US-5500532-\$).did. or		
	1	(US-20020000666-\$ or US-20020190350-\$ or		
		US-20020168820-\$).did. or		
		(JP-03044703-\$).did. or (US-5761115-\$ or US-6348365-\$ or EP-846353-\$).did.		
_	13		USPAT;	2003/11/23 11:29
		"ge.sub."??"Se.sub."\$5	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	100	501/11	IBM_TDB USPAT	2003/11/23 15:40
_	193 199	501/11   501/11	USPAT;	2003/11/23 15:40
_	199		US-PGPUB	2003,11,23 13.40
-	279	501/19	USPAT;	2003/11/23 15:40
			US-PGPUB	0000 /11 /00 15 15
-	192	501/42	USPAT; US-PGPUB	2003/11/23 15:40
_	0	501/11 and 501/19 and 501/42	USPAT;	2003/11/23 15:40
		301/11 una 301/13 una 301/12	US-PGPUB	2003,11,23 13.10
_	3	501/19 and 501/42	USPAT;	2003/11/23 15:57
	_		US-PGPUB	0000 /11 /00 15 10
-	8	germanium and selenium and chalcogenide and silver and phase adj transition	USPAT; US-PGPUB;	2003/11/23 16:42
		and silver and phase adj transition	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	JP-03044703\$-\$.DID.	USPAT;	2003/11/23 16:57
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	14	(("6388324") or ("20020000666") or	USPAT;	2004/06/11 13:24
		("5500532") or ("6418049") or ("5751012")	US-PGPUB	
		or ("5789277") or ("6348365") or		
		("20020168820") or ("6469364") or ("6348365") or ("6418049") or ("5761115")		
		or ("5896312") or ("5914893") or		
		("6084796") or ("6635914")).PN.		
-	3	((("6388324") or ("20020000666") or	USPAT;	2004/06/10 18:35
		("5500532") or ("6418049") or ("5751012")	US-PGPUB;	
	ĺ	or ("5789277") or ("6348365") or ("20020168820") or ("6469364") or	EPO; JPO; DERWENT;	
		("6348365") or ("6418049") or ("5761115")	IBM TDB	
		or ("5896312") or ("5914893") or		
		("6084796") or ("6635914")).PN.) and		
		\$6"Ge.sub."\$6 ((("6388324") or ("20020000666") or	HCDATT.	2004/06/10 18:35
-	2	(("6388324") or ("2002000666") or ("5751012")	USPAT; US-PGPUB;	2004/00/10 18:35
		or ("5789277") or ("6348365") or	EPO; JPO;	
		("20020168820") or ("6469364") or	DERWENT;	
		("6348365") or ("6418049") or ("5761115")	IBM_TDB	
		or ("5896312") or ("5914893") or		
		("6084796") or ("6635914")).PN.) and \$6"Ge.sub."\$6 near6 (glass amorphous)		
-	2	("6487106").PN.	USPAT;	2004/06/11 10:31
			US-PGPUB;	
			EPO; JPO;	
]			DERWENT; IBM TDB	
	1	<u> </u>	TD03_1D0	l

	_			
	2	("5761115").PN.	USPAT;	2004/06/11 11:22
			US-PGPUB;	
1	ļ		EPO; JPO;	[
			DERWENT;	
	i		IBM_TDB	
-	13		USPAT;	2004/06/11 11:34
		memory adj cell and (non-volatile	US-PGPUB;	
	1	nonvolatile)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
l –	13	chalcogenide adj glass and "Ge.sub."\$6 and	USPAT;	2004/06/11 11:35
		memory adj cell and (non-volatile	US-PGPUB;	
		nonvolatile) and (silver Ag)	EPO; JPO;	
			DERWENT;	
1			IBM TDB	
_	13	chalcogenide adj glass and "Ge.sub."\$6 and	USPAT;	2004/06/11 11:40
		memory adj cell and (non-volatile	US-PGPUB;	
		nonvolatile) and (silver Ag) and	EPO; JPO;	
	}	(semiconductor semiconducting)	DERWENT;	
		(00200	IBM TDB	1
l _	24	(semiconductor semiconducting) near4	USPAT;	2004/06/11 11:41
1		(glass glasses) and "Ge.sub."\$9 and	US-PGPUB;	
1		(non-volatile non-volatile)	EPO; JPO;	
1		(11011 VOIGETIC HOIL VOIGETIE)	DERWENT;	, ,
			IBM TDB	
l _	20	(semiconductor semiconducting) near2	USPAT;	2004/06/11 11:42
-	20	(glass glasses) and "Ge.sub."\$9 and	US-PGPUB;	2004/00/11 11:42
	]	(grass grasses) and "Ge.sub."39 and (non-volatile non-volatile)		
	]	(non-volatile non-volatile)	EPO; JPO;	
			DERWENT;	
	1 22	/comiconducton comiconduction\	IBM_TDB	3004/06/31 11:40
-	20	(semiconductor semiconducting) near2	USPAT;	2004/06/11 11:42
		(glass glasses) and "Ge.sub."\$9 and	US-PGPUB;	
		(non-volatile non-volatile) and memory	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	8	(semiconductor semiconducting) near2	USPAT;	2004/06/11 11:42
		(glass glasses) and "Ge.sub."\$9 and	US-PGPUB;	
		(non-volatile non-volatile) and memory and	EPO; JPO;	
		\$6"Se.sub."\$3	DERWENT;	į į
			IBM_TDB	
-	14		USPAT;	2004/06/11 13:25
		US-5789277-\$ or US-6635914-\$ or	US-PGPUB	
		US-5500532-\$ or US-6469364-\$ or		
!		US-5751012-\$ or US-5761115-\$ or		
		US-6388324-\$ or US-6418049-\$ or		
		US-6348365-\$ or US-6084796-\$).did. or		
	[	(US-20020000666-\$ or		
		US-20020168820-\$).did.		
-	0	wo-0221542\$-\$.did.	USPAT;	2004/06/11 13:25
			US-PGPUB;	i l
			EPO; JPO;	
			DERWENT;	1
			IBM_TDB	
-	1	wo-200221542\$-\$.did.	USPAT;	2004/06/11 13:26
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	Į į
<b>-</b> .	1	wo-200048196\$-\$.did.	USPAT;	2004/06/11 13:27
			US-PGPUB;	
l i			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	0	wo-199748032\$-\$.did.	USPĀT;	2004/06/11 13:27
			US-PGPUB;	
			EPO; JPO;	[
			DERWENT;	
			IBM TDB	

				T
-	1	wo-9748032\$-\$.did.	USPAT; US-PGPUB;	2004/06/11 13:28
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	1
-	2	wo-9928914\$-\$.did.	USPAT;	2004/06/11 13:28
			US-PGPUB;	
			EPO; JPO;	į
			DERWENT; IBM TDB	
l _	l 0	"Ge.sub.x Se.sub.1-x"\$6 and silver and	USPAT;	2004/06/11 15:00
1		chalcogenide adj glass and (semiconductor	US-PGPUB;	2001,00,11 10.00
		semiconducting) and memory	EPO; JPO;	
			DERWENT;	
	0.7		IBM_TDB	0004/06/11 10 26
_	27	1	USPAT; US-PGPUB;	2004/06/11 18:36
		adj glass and (semiconductor semiconducting) and memory	EPO; JPO;	
	]	Semiconducting, and memory	DERWENT;	
			IBM TDB	
-	18	kozicki.in. and "0.5"	USPAT;	2004/06/11 18:36
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	11	kozicki.in. and "0.5" and "0.1"	USPAT;	2004/06/11 18:40
			US-PGPUB;	
†			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/06/10 10 00
_	9	kozicki.in. and "0.5" same "0.1"	USPAT;	2004/06/12 12:28
ŀ			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	9	(mitkova.in. kozicki.in.) and "0.5" same	USPĀT;	2004/06/11 19:28
		"0.1"	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	20	(mitkova.in. kozicki.in.) and ("0.4" "0.5"	USPAT;	2004/06/11 19:29
ĺ		"0.6")	US-PGPUB;	
İ			EPO; JPO;	
			DERWENT;	
_	_	(mitkova.in. kozicki.in.) and ("0.4" "0.5"	IBM_TDB USPAT;	2004/06/11 19:29
-	9	(mitkova.in. kozicki.in.) and ("0.4" "0.5"   "0.6") same x	US-PGPUB;	2004/00/11 19:29
		o.o, same a	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	jp-03044703\$-\$.did.	USPAT;	2004/06/12 12:30
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	818		USPAT;	2004/06/12 12:31
		memory adj cell and ("same chip" "single	US-PGPUB;	_
		chip")	EPO; JPO;	
[			DERWENT;	
_	52	integrated adj circuit same processor same	IBM_TDB USPAT;	2004/06/12 13:04
		memory adj cell and ("same chip" "single	US-PGPUB;	2007/00/12 13:04
		chip")	EPO; JPO;	
		-	DERWENT;	
			IBM_TDB	0004/05/50 55 51
-	18		USPAT;	2004/06/12 13:11
		<pre>memory adj cell same ("same chip" "single chip")</pre>	US-PGPUB; EPO; JPO;	
		CHIP /	DERWENT;	
,			IBM TDB	
		Water the second		<del></del>

-	0	integrated adj circuit same processor same memory adj cell same ("same chip" "single chip") same (non-volatile nonvolatile)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/12 13:11
-	0	(IC integrated adj circuit) same processor same memory adj cell same ("same chip" "single chip") same (non-volatile nonvolatile)	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/12 14:22